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Quad 2-Channel Multiplexer

The MC74VHCT157A is an advanced high speed CMOS quad 2–channel multiplexer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

It consists of four 2-input digital multiplexers with common select (S) and enable (\overline{E}) inputs. When \overline{E} is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the A or B inputs get routed to the corresponding Y outputs.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V because it has full 5.0 V CMOS level output swings.

The VHCT157A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage–input/output voltage mismatch, battery backup, hot insertion, etc.

The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

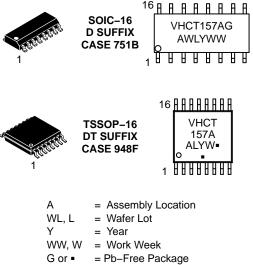
- High Speed: $t_{PD} = 4.1$ ns (Typ) at $V_{CC} = 5.0$ V
- Low Power Dissipation: $I_{CC} = 4 \ \mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL–Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 V (Max)$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:
 - Human Body Model > 2000 V; Machine Model > 200 V
- Chip Complexity: 82 FETs or 20 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



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MARKING DIAGRAMS



(Note: Microdot may be in either location)

FUNCTION TABLE

Inp	Outputs	
E	s	Y0 – Y3
Н	Х	L
L	L	A0-A3
L	Н	B0-B3

A0 - A3, B0 - B3 = the levels of the respective Data–Word Inputs.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

s[1 •	16	v _{cc}
A0 [2	15	ΠE
B0 [3	14] A3
Y0 [4	13] B3
A1 [5	12] Y3
B1 [6	11] A2
Y1 [7	10] в2
GND [8	9] Y2

Figure 1. Pin Assignment

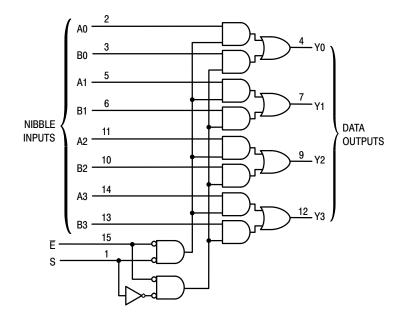


Figure 2. Expanded Logic Diagram

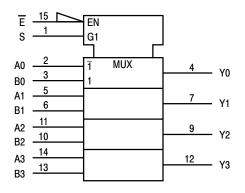


Figure 3. IEC Logic Symbol

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

MAXIMUM RATINGS (Note 1)

Symbol	P	arameter	Value	Unit
V _{CC}	Positive DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	Digital Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	Output in 3–State High or Low State	–0.5 to +7.0 –0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current		-20	mA
I _{ОК}	Output Diode Current		±20	mA
lout	DC Output Current, per Pin		±25	mA
Icc	DC Supply Current, V _{CC} and GND Pi	ins	±75	mA
PD	Power Dissipation in Still Air	SOIC TSSOP	200 180	mW
T _{STG}	Storage Temperature Range		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 >200	V
I _{LATCHUP}	Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 5)	± 300	mA
θ_{JA}	Thermal Resistance, Junction-to-Arr	nbient SOIC TSSOP	143 164	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

2. Tested to EIA/JESD22-A114-A

Tested to EIA/JESD22-A115-A 3.

4. Tested to JESD22-C101-A

5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	DC Supply Voltage	4.5	5.5	V
V _{IN}	DC Input Voltage	0	5.5	V
V _{OUT}		tput in 3–State 0 h or Low State	V _{CC}	V
T _A	Operating Temperature Range, all Package Types	-55	125	°C
t _r , t _f	Input Rise or Fall Time V _{CC} =	= 5.0 V <u>+</u> 0.5 V 0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

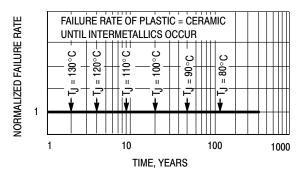


Figure 4. Failure Rate vs. Time Junction Temperature

DC CHARACTERISTICS (Voltages Referenced to GND)

			v _{cc}	T _A = 25°C		V _{CC} T _A = 25		T _A ≤	85°C		≤ T _A ≤ 5°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit	
V _{IH}	Minimum High–Level Input Voltage		4.5 to 5.5	2			2	0.8	2		V	
VIL	Maximum Low–Level Input Voltage		4.5 to 5.5			0.8		0.8		0.8	V	
V _{OH}	Maximum High–Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	4.5	4.4	4.5		4.4		4.4		V	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -8 \text{ mA}$	4.5	3.94			3.8		3.66			
V _{OL}	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu\text{A}$	4.5		0.0	0.1		0.1		0.1	V	
		V _{IN} = V _{IH} or V _{IL} I _{OH} = 8 mA	4.5			0.36		0.44		0.52		
I _{IN}	Input Leakage Current	$V_{IN} = 5.5 \text{ V or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μΑ	
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40.0		40.0	μΑ	
I _{CCT}	Additional Quiescent Supply Current (per Pin)	Any one input: $V_{IN} = 3.4 V$ All other inputs: $V_{IN} = V_{CC} \text{ or GND}$	5.5			1.35		1.5		1.5	μΑ	
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0			0.5		5		5	μΑ	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

				т	A = 25°	с	T_A = ≤	≤ 85°C		≤ T _A ≤ 5°C	
Symbol	Parameter	Test Condit	ions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay; A to B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		5.6 8.0	7.0 10.0	1.0 1.0	7.7 11.0	1.0 1.0	7.7 11.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		4.1 5.6	6.4 8.4	1.0 1.0	7.5 9.5	1.0 1.0	7.5 9.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; S to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		6.1 8.5	7.5 10.5	1.0 1.0	8.2 11.5	1.0 1.0	8.2 11.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15pF C _L = 50pF		5.3 6.8	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; E to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		6.1 8.5	7.5 10.5	1.0 1.0	8.2 11.5	1.0 1.0	8.2 11.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		5.6 7.1	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	10.0 12.0	
C _{IN}	Maximum Input Capacitance				4	10		10		10	pF
					Ту	pical @	25°C,	V _{CC} = 5	.0 V		
C _{PD}	Power Dissipation Capacitance	(Note 6)		20			pF				

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} ● V_{CC} ● f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} ● V_{CC}² ● f_{in} + I_{CC} ● V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T _A =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	- 0.3	- 0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

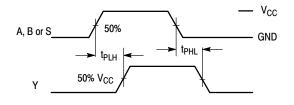


Figure 5. Switching Waveform

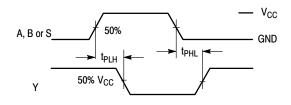
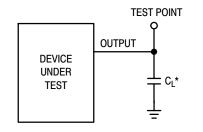


Figure 6. Inverting Switching



*Includes all probe and jig capacitance

Figure 7. Test Circuit

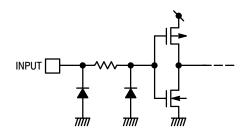


Figure 8. Input Equivalent Circuit

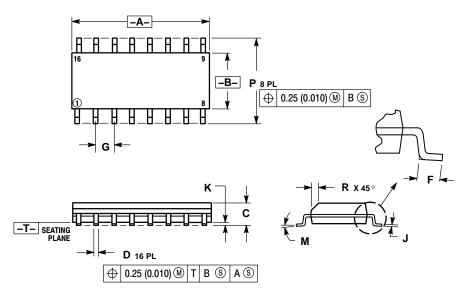
ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT157ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74VHCT157ADR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC74VHCT157ADTG	TSSOP-16 (Pb-Free)	96 Units / Rail
M74VHCT157ADTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

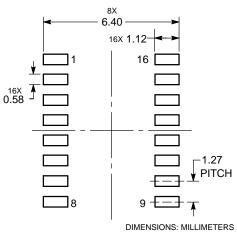
SOIC-16 CASE 751B-05 ISSUE K



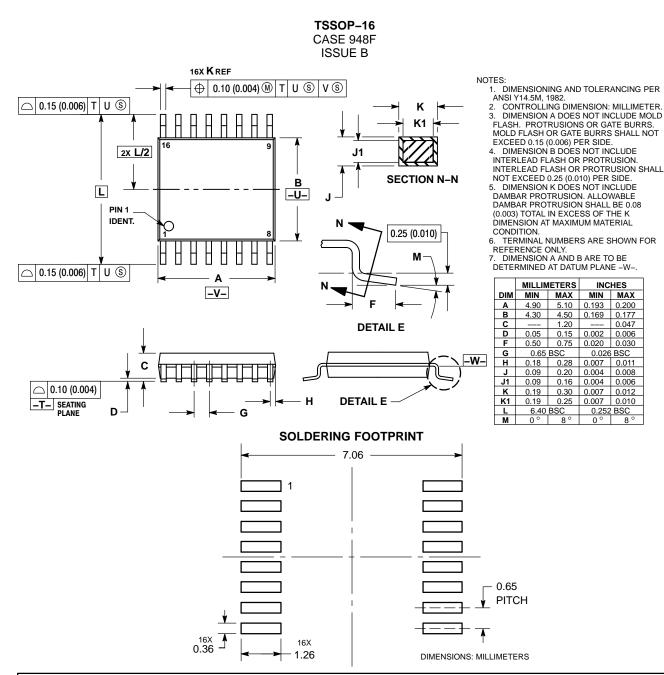
NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES			
DIM	MIN	MAX	MIN	MAX			
Α	9.80	10.00	0.386	0.393			
В	3.80	4.00	0.150	0.157			
С	1.35	1.75 0.054	0.054 0.	0.068			
D	0.35	0.49	0.014	0.019			
F	0.40	1.25	0.016	0.049			
G	1.27	BSC	0.050) BSC			
J	0.19	0.25	0.008	0.009			
Κ	0.10	0.25	0.004	0.009			
М	0 °	7°	0 °	7°			
Ρ	5.80	6.20	0.229	0.244			
R	0.25	0.50	0.010	0.019			

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS



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